

First Named Inventor	Leonard Forbes	INFORMATION DISCLOSURE STATEMENT FORM PTO-1449
Serial No.	10/681,408	
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Examiner Name	Unknown	
Confirmation No.	7405	
Attorney Docket No.	400.250US01	
Title: VERTICAL NROM HAVING A STORAGE DENSITY OF 1 BIT PER 1F2		Sheet 1 of 7

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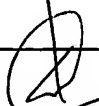
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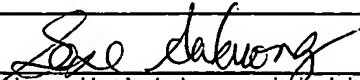
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